



SI7309DN-T1-GE3 Information



For Reference Only

Part Number SI7309DN-T1-GE3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 60V 8A 1212-8 PPAK

Package PowerPAK? 1212-8

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SI7309DN-T1-GE3 Specifications

| Manufacturer Part Number SI7309DN-T1-GE3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package PowerPAK? 1212-8 Series TrenchFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 22nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 600pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.2W (Ta), 19.8W (Tc) Rds On (Max) @ Id, Vgs 115 mOhm @ 3.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? 1212-8 Package / Case PowerPAK? 1212-8 | | |
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| Series TrenchFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 22nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 600pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.2W (Ta), 19.8W (Tc) Rds On (Max) @ Id, Vgs 115 mOhm @ 3.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? 1212-8 Package / Case PowerPAK? 1212-8 | | Transistors - FETs, MOSFETs - Single |
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| TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 10VInput Capacitance (Ciss) (Max) @ Vds600pF @ 30VVgs (Max)±20VFET Feature-Power Dissipation (Max)3.2W (Ta), 19.8W (Tc)Rds On (Max) @ Id, Vgs115 mOhm @ 3.9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? 1212-8Package / CasePowerPAK? 1212-8 | Series | TrenchFET? |
| Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 10VInput Capacitance (Ciss) (Max) @ Vds600pF @ 30VVgs (Max)±20VFET Feature-Power Dissipation (Max)3.2W (Ta), 19.8W (Tc)Rds On (Max) @ Id, Vgs115 mOhm @ 3.9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? 1212-8Package / CasePowerPAK? 1212-8 | FET Type | P-Channel |
| Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1nput Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 115 mOhm @ 3.9A, 10V Operating Temperature Supplier Device Package PowerPAK? 1212-8 PowerPAK? 1212-8 PowerPAK? 1212-8 | Technology | MOSFET (Metal Oxide) |
| Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 10VInput Capacitance (Ciss) (Max) @ Vds600pF @ 30VVgs (Max)±20VFET Feature-Power Dissipation (Max)3.2W (Ta), 19.8W (Tc)Rds On (Max) @ Id, Vgs115 mOhm @ 3.9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? 1212-8Package / CasePowerPAK? 1212-8 | Drain to Source Voltage (Vdss) | 60V |
| Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1nput Capacitance (Ciss) (Max) @ Vds 600pF @ 30V Vgs (Max) +20V FET Feature - Power Dissipation (Max) 3.2W (Ta), 19.8W (Tc) Rds On (Max) @ Id, Vgs 115 mOhm @ 3.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? 1212-8 Package / Case | Current - Continuous Drain (Id) @ 25°C | 8A (Tc) |
| Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 600pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 115 mOhm @ 3.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? 1212-8 Package / Case | Drive Voltage (Max Rds On, Min Rds On) | 4.5V, 10V |
| Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 115 mOhm @ 3.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case PowerPAK? 1212-8 PowerPAK? 1212-8 | Vgs(th) (Max) @ Id | 3V @ 250μA |
| Vgs (Max)±20VFET Feature-Power Dissipation (Max)3.2W (Ta), 19.8W (Tc)Rds On (Max) @ Id, Vgs115 mOhm @ 3.9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? 1212-8Package / CasePowerPAK? 1212-8 | Gate Charge (Qg) (Max) @ Vgs | 22nC @ 10V |
| FET Feature - Power Dissipation (Max) 3.2W (Ta), 19.8W (Tc) Rds On (Max) @ Id, Vgs 115 mOhm @ 3.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? 1212-8 Package / Case PowerPAK? 1212-8 | Input Capacitance (Ciss) (Max) @ Vds | 600pF @ 30V |
| Power Dissipation (Max) Rds On (Max) @ Id, Vgs 115 mOhm @ 3.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? 1212-8 Package / Case PowerPAK? 1212-8 | Vgs (Max) | ±20V |
| Rds On (Max) @ Id, Vgs 115 mOhm @ 3.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? 1212-8 Package / Case PowerPAK? 1212-8 | FET Feature | - |
| Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? 1212-8 Package / Case PowerPAK? 1212-8 | Power Dissipation (Max) | 3.2W (Ta), 19.8W (Tc) |
| Mounting Type Surface Mount Supplier Device Package PowerPAK? 1212-8 Package / Case PowerPAK? 1212-8 | Rds On (Max) @ Id, Vgs | 115 mOhm @ 3.9A, 10V |
| Supplier Device Package PowerPAK? 1212-8 Package / Case PowerPAK? 1212-8 | Operating Temperature | -55°C ~ 150°C (TJ) |
| Package / Case PowerPAK? 1212-8 | Mounting Type | Surface Mount |
| | Supplier Device Package | PowerPAK? 1212-8 |
| Report errors? | Package / Case | PowerPAK? 1212-8 |
| | | Report errors? |

SI7309DN-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI7309DN-T1-GE3 Payment Methods



















SI7309DN-T1-GE3 Shipping Methods













If you have any question about SI7309DN-T1-GE3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com